

IN THE SPECIFICATION

Please replace the paragraph [0033] at pages 6-7, with the following rewritten paragraph:

[0033] In another aspect of the present invention (hereinafter referred to as “second invention”), a method for fabricating a semiconductor optical device is provided including the steps of: forming a first stacked structure including either of a DFB laser having a quantum-well-structure active layer made of a GaInAsP-based material and or an EA modulator having a quantum-well-structure active layer made of an AlGaInAs-based material in a DFB laser formation area and in an EA modulator formation area, respectively, on a semiconductor substrate; forming a second stacked structure by etching the area corresponding to the other of the DFB laser and or the EA modulator to expose the substrate in the DFB laser formation this area or in the EA modulator formation area; forming a third stacked structure including the other of the DFB laser and or the EA modulator on the exposed substrate; and forming a mesa stripe by simultaneously etching the second and third stacked structures.